

AMENDMENT TO THE CLAIMS:

1. (Currently Amended) A semiconductor device comprising:

n (n is an integer equal to or greater than 2) thin film transistors provided between an element to be driven which operates based on supplied power and a power supply line for supplying power to said element to be driven, for controlling, in accordance with a data signal, power supplied to said element to be driven; wherein

the number of contact points for electrically connecting said n thin film transistors and corresponding element to be driven is equal to or less than (n-1).

2. (Original ) A semiconductor device according to claim 1, wherein

said n thin film transistors and corresponding element to be driven are electrically connected to each other by a wiring layer; and

the contact position between the wiring layer and the thin film transistor is placed to be distant from the contact position between the wiring layer and said element to be driven.

3. (Original ) A semiconductor device according to claim 2, wherein

said element to be driven is an emissive element which includes an emissive element layer between a first electrode and a second electrode;

a contact hole is formed on an insulation layer which is formed above said wiring layer, said wiring layer being connected through the contact hole to said first electrode of said emissive element which is formed on top of said insulation layer and covering said contact hole;

at least the contact hole region of said first electrode is covered by a flattening layer; and said emissive element layer is formed above said first electrode and said flattening layer.

4. (Original) A semiconductor device according to claim 1, wherein

said n thin film transistors and corresponding element to be driven are directly or indirectly and electrically connected to each other at a contact hole formed on an insulation layer for separating said thin film transistor which is formed at a lower layer and said element to be driven;

at least the contact hole region of said first electrode is covered by a flattening layer; and an emissive element layer is formed above said first electrode and said flattening layer.

5. (Original) A semiconductor device according to claim 1, wherein said element to be driven is an organic electroluminescence element which uses an organic compound in an emissive layer.

6. (New) A semiconductor device comprising:

n (n is an integer equal to or greater than 2) thin film transistors provided between an element to be driven which operates based on supplied power and a power supply line for supplying power to said element to be driven, for controlling power supplied to said element to be driven; and

a switching thin film transistor connected to a data line, for operating in accordance with a gate signal to capture a data signal from said data line; wherein

each of said n thin film transistors supplies power from said power supply line to said element to be driven, in accordance with said data signal captured by said switching thin film transistor, and

the number of contact points for electrically connecting said n thin film transistors and corresponding element to be driven is equal to or less than (n-1).

7. (New) A semiconductor device according to claim 6, wherein said element to be driven is a current-driven electroluminescence element.